MGBR5L150 Preliminary DIODE

# MOS GATED BARRIER RECTIFIER

#### **■** DESCRIPTION

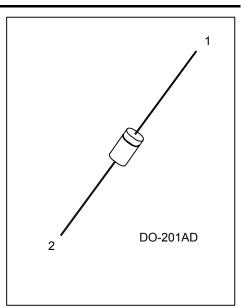
The UTC MGBR5L150 is a surface mount mos gated barrier rectifier, it uses UTC's advanced technology to provide customers withlow forward voltage drop and high switching speed, etc.

#### ■ FEATURES

- \* Low forward voltage drop
- \* High switching speed

# ■ SYMBOL

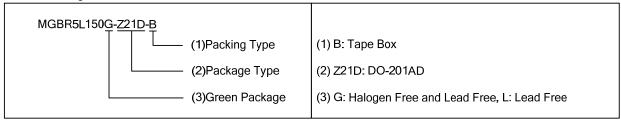




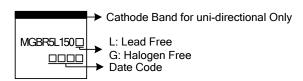
#### ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment		Dooking	
Lead Free	Halogen Free	Package	1	2	Packing	
MGBR5L150L-Z21D-R	MGBR5L150G-Z21D-R	DO-201AD	K	Α	Tape Box	

Note: Pin Assignment: A: Anode K: Cathode



#### MARKING



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## ■ ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C, unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER		SYMBOL	RATINGS	UNIT
DC Blocking Voltage		$V_{RM}$	150	V
Working Peak Reverse Voltage		$V_{RWM}$	150	V
Repetitive Peak Reverse Voltage		$V_{RRM}$	150	V
RMS Reverse Voltage		$V_{R(RMS)}$	105	V
Average Rectified Output Current	T <sub>C</sub> =80°C	Ιο	5	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load		I <sub>FSM</sub>	150	Α
Operating Junction Temperature		$T_J$	-65 ~ +150	°C
Storage Temperature		$T_{STG}$	-65 ~ <b>+</b> 150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### ■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$\theta_{JA}$	50	°C/W
Junction to Case	θ <sub>JC</sub>	12	°C/W

### ■ **ELECTRICAL CHARACTERISTICS**(T<sub>A</sub>=25°C,unless otherwise specified.)

PARAMETER SYMBO		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	I <sub>R</sub> =0.5mA	150			V
Forward Voltage Drop	$V_{FM}$	I <sub>F</sub> =5A, T <sub>J</sub> =25°C			0.86	V
		I <sub>F</sub> =5A, T <sub>J</sub> =125°C			0.73	V
Leakage Current (Note 1)	I PM	V <sub>R</sub> =150V, T <sub>J</sub> =25°C			100	μA
		V <sub>R</sub> =150V, T <sub>J</sub> =125°C			20	mA

Notes: 1. Short duration pulse test used to minimize self-heating effect.

<sup>2.</sup> Thermal resistance junction to case mounted on heatsink.

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